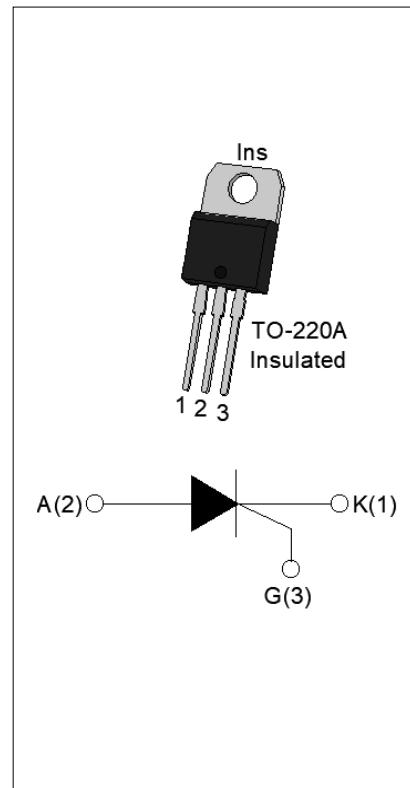




JCT1225A 25A SCR

Rev.A.1.0

With high ability to withstand the shock loading of large current, JCT1225A SCR provides high dV/dt rate with strong resistance to electromagnetic interference. It is especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc. From all three terminals to external heatsink, JCT1225A provides a rated insulation voltage of 2500 V_{RMS}, complying with UL standards (File ref: E252906). Package TO-220A is RoHS compliant.



Symbol	Value	Unit
I _{T(RMS)}	25	A
V _{DRM/V_{RRM}}	1200	V
I _{GT}	40	mA

Parameter	Symbol	Value	Unit
Storage junction temperature range	T _{stg}	-40-150	°C
Operating junction temperature range	T _j	-40-125	°C
Repetitive peak off-state voltage (T _j =25°C)	V _{DRM}	1200	V
Repetitive peak reverse voltage (T _j =25°C)	V _{RRM}	1200	V
Average on-state current (T _c ≤64°C)	I _{T(AV)}	16	A
RMS on-state current (T _c ≤64°C)	I _{T(RMS)}	25	A
Non repetitive surge peak on-state current (t _p =10ms, T _j =25°C)	I _{TSM}	320	A
Non repetitive surge peak on-state current (t _p =8.3ms, T _j =25°C)		352	
I ² t value for fusing (t _p =10ms, T _j =25°C)	I ² t	512	A ² s
Critical rate of rise of on-state current (I _G =2 I _{GT} , f=100Hz, T _j =125°C)	dI/dt	200	A s

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Peak gate current ($t_p=20\text{ s}$, $T_j=125^\circ\text{C}$)	I_{GM}	5	A
Average gate power dissipation ($T_j=125^\circ\text{C}$)	$P_{G(AV)}$	1	W
Peak gate power			
Peak pulse voltage ($T_j=25^\circ\text{C}$; non-repetitive, off-state; FIG.7)			

Symbol	Test Condition	Value		Unit
		MIN.	TYP.	
		M/0.0X (05)	TJ	0 Tc 0 Tw 2.1

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FIG.1 Maximum power dissipation versus RMS on-state current

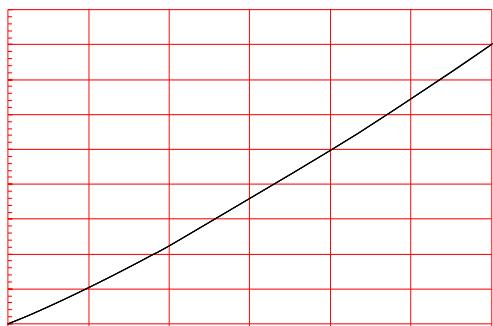
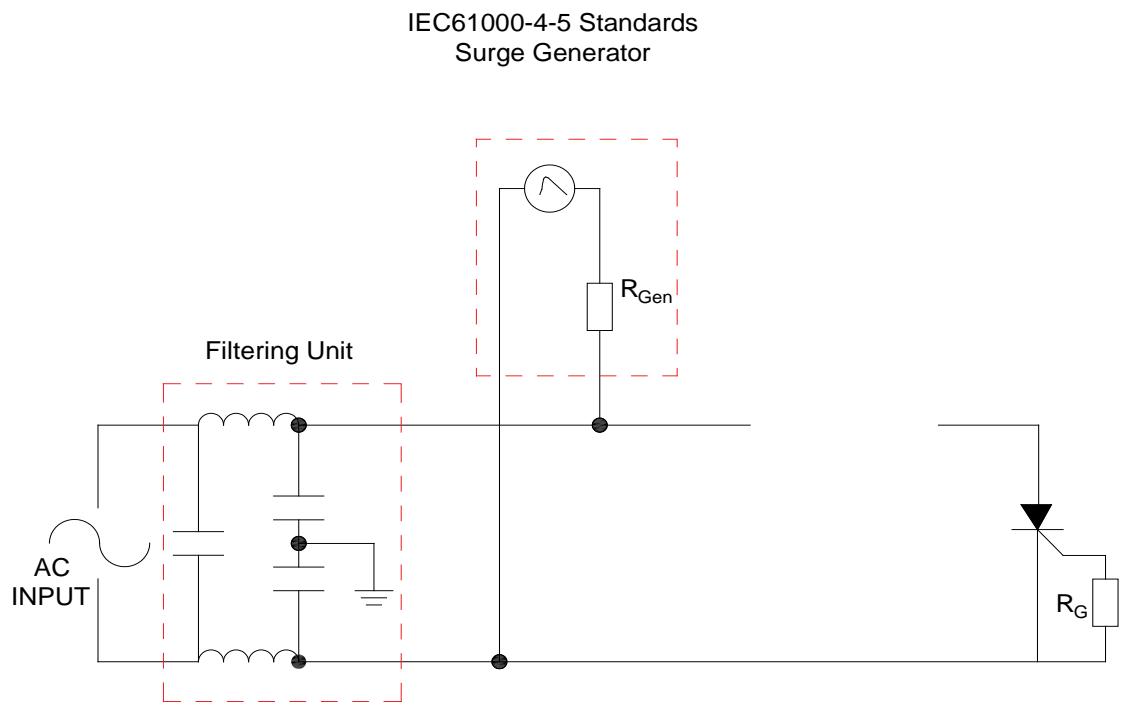


FIG.2: RMS on-state current versus case temperature

FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT1225A	1200	40	TO-220A(Ins)	50	Tube

Document Revision History

Date	Revision	Changes
Apr.13, 2023	A.1.0	Last update

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